

Hsien-Wen Wan

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6174368/publications.pdf>

Version: 2024-02-01

22
papers

96
citations

1684188
5
h-index

1474206
9
g-index

22
all docs

22
docs citations

22
times ranked

75
citing authors

#	ARTICLE	IF	CITATIONS
1	Surface electronic structure of epi germanium (001)-2 Å— 1. Applied Physics Express, 2017, 10, 075701.	2.4	16
2	Perfecting the Al ₂ O ₃ /In _{0.53} Ga _{0.47} As interfacial electronic structure in pushing metal-oxide-semiconductor field-effect-transistor device limits using <i>in-situ</i> atomic-layer-deposition. Applied Physics Letters, 2017, 111, .	3.3	15
3	Atomic Nature of the Growth Mechanism of Atomic Layer Deposited High- $\hat{\nu}$ Y ₂ O ₃ on GaAs(001)-4 Å— 6 Based on <i>in Situ</i> Synchrotron Radiation Photoelectron Spectroscopy. ACS Omega, 2018, 3, 2111-2118.	3.5	8
4	Low-Temperature-Grown Single-Crystal Si Epitaxially on Ge, Followed by Direct Deposition of High- $\hat{\nu}$ Dielectrics—Attainment of Low Interfacial Traps and Highly Reliable Ge MOS. ACS Applied Electronic Materials, 2021, 3, 2164-2169.	4.3	8
5	Low-temperature grown single-crystal Si on <i>epi</i> Ge(001)-2 Å— 1 and its oxidation: electronic structure study via synchrotron radiation photoemission. Applied Physics Express, 2020, 13, 085504.	2.4	7
6	<i>In situ</i> Y ₂ O ₃ on <i>p</i> -In _{0.53} Ga _{0.47} As—Attainment of low interfacial trap density and thermal stability at high temperatures. Applied Physics Letters, 2021, 118, .	3.3	6
7	Surface electronic structure of Si _{1-x} Ge _x (001)-2 Å— 1: a synchrotron radiation photoemission study. Applied Physics Express, 2020, 13, 095503.	2.4	6
8	Exciton Localization of High-Quality ZnO/Mg _x Zn _{1-x} O Multiple Quantum Wells on Si (111) with a Y ₂ O ₃ Buffer Layer. ACS Applied Nano Materials, 2018, 1, 3829-3836.	5.0	5
9	Microscopic Views of Atomic and Molecular Oxygen Bonding with epi Ge(001)-2 Å— 1 Studied by High-Resolution Synchrotron Radiation Photoemission. Nanomaterials, 2019, 9, 554.	4.1	5
10	Attainment of low subthreshold slope in planar inversion-channel InGaAs MOSFET with <i>in situ</i> deposited Al ₂ O ₃ /Y ₂ O ₃ as a gate dielectric. Japanese Journal of Applied Physics, 2022, 61, SC1018.	1.5	4
11	BTI Characterization of MBE Si-Capped Ge Gate Stack and Defect Reduction via Forming Gas Annealing. , 2019, , .		3
12	Epitaxy of High-Quality Single-Crystal Hexagonal Perovskite YAlO ₃ on GaAs(111)A Using Laminated Atomic Layer Deposition. Crystal Growth and Design, 2019, 19, 2030-2036.	3.0	3
13	Atomic layer deposited single-crystal hexagonal perovskite YAlO ₃ epitaxially on GaAs(111)A. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, 01B123.	2.1	2
14	<i>In-situ</i> deposited HfO ₂ and Y ₂ O ₃ on epi-Si/p-Ge—a comparative study of the interfacial properties and reliability. Japanese Journal of Applied Physics, 2022, 61, SC1074.	1.5	2
15	A Synchrotron Radiation Photoemission Study of SiGe(001)-2Å—1 Grown on Ge and Si Substrates: The Surface Electronic Structure for Various Ge Concentrations. Nanomaterials, 2022, 12, 1309.	4.1	2
16	Fundamental Understanding of Oxide Defects in HfO ₂ and Y ₂ O ₃ on GaAs(001) with High Thermal Stability. , 2019, , .		1
17	Scavenging Segregated Ge on Thin Single-Crystal Si Epitaxially Grown on Ge. ACS Applied Electronic Materials, 0, , .	4.3	1
18	Low thermal budget epitaxial lift off (ELO) for Ge (111)-on-insulator structure. Japanese Journal of Applied Physics, 2022, 61, SC1024.	1.5	1

#	ARTICLE	IF	CITATIONS
19	High-Ge-Content Si _{1-x} Ge _x Gate Stacks with Low-Temperature Deposited Ultrathin Epitaxial Si: Growth, Structures, Low Interfacial Traps, and Reliability. ACS Applied Electronic Materials, 2022, 4, 2641-2647.	4.3	1
20	Oxidation and hydrogenation of SiGe(0 0 1)-2Å–Å1 at room temperature and in situ annealing: A synchrotron radiation photoemission study. Applied Surface Science, 2021, 569, 150962.	6.1	0
21	(Invited) Thin Epitaxial Single-Crystal Si on SiGe Followed By in-Situ Deposition of High-k Dielectrics “Novel Gate Stacks for Achieving Extremely Low D _{it} and Highly Reliable SiGe MOS. ECS Meeting Abstracts, 2022, MA2022-01, 1067-1067.	0.0	0
22	Microscopic Views of Ge Segregation and Scavenging Ge on Thin Si on Epi-Ge(001). ECS Meeting Abstracts, 2022, MA2022-01, 1053-1053.	0.0	0